

ABSTRACT

A magnetic memory device includes a substrate, a patterned conductive layer, and a magnetic tunnel junction (MTJ) structure. The substrate includes a memory area and a circuit area. The patterned conductive layer includes a first
5 conductive pattern and a second conductive pattern that are separated from each other. The first conductive pattern is disposed in the memory area, and the second conductive pattern is disposed in the circuit area. The MTJ structure is disposed on the first conductive pattern and electrically contact with the first conductive pattern.

10 FIG. 2F